

Sima Dimitrijević

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

260 papers	4,649 citations	34 h-index	56 g-index
296 ext. papers	5,205 ext. citations	2.4 avg, IF	5.46 L-index

#	Paper	IF	Citations
260	A Figure of Merit for Selection of the Best Family of SiC Power MOSFETs. <i>Electronics (Switzerland)</i> , 2022 , 11, 1433	2.6	1
259	Image Force Corrections to Tungsten Inhomogeneous Schottky Barrier Model. <i>IEEE Transactions on Electron Devices</i> , 2021 , 1-7	2.9	
258	AlGaN/GaN 2-D Electron Gas for Highly Sensitive and High-Temperature Current Sensing. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1495-1500	2.9	2
257	. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2021 , 1-1	2.6	
256	Fast Near-Interface Traps in 4H-SiC MOS Capacitors Measured by an Integrated-Charge Method. <i>IEEE Access</i> , 2021 , 9, 109745-109753	3.5	3
255	A method for characterizing near-interface traps in SiC metal-oxide-semiconductor capacitors from conductance-temperature spectroscopy measurements. <i>Journal of Applied Physics</i> , 2021 , 129, 054501	2.5	0
254	Modeling Power GaN-HEMTs Using Standard MOSFET Equations and Parameters in SPICE. <i>Electronics (Switzerland)</i> , 2021 , 10, 130	2.6	3
253	A Simple Equation for the Energy Stored by Voltage-Dependent Capacitances. <i>IEEE Transactions on Power Electronics</i> , 2020 , 35, 12629-12632	7.2	
252	Near-Interface Trap Model for the Low Temperature Conductance Signal in SiC MOS Capacitors With Nitrided Gate Oxides. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3722-3728	2.9	4
251	Measurement of Power Dissipation Due to Parasitic Capacitances of Power MOSFETs. <i>IEEE Access</i> , 2020 , 8, 187043-187051	3.5	1
250	Thermoresistance of p-Type 4H-SiC Integrated MEMS Devices for High-Temperature Sensing. <i>Advanced Engineering Materials</i> , 2019 , 21, 1801049	3.5	7
249	Energy-Localized Near-Interface Traps Active in the Strong-Accumulation Region of 4H-SiC MOS Capacitors. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1704-1709	2.9	0
248	Description and Verification of the Fundamental Current Mechanisms in Silicon Carbide Schottky Barrier Diodes. <i>Scientific Reports</i> , 2019 , 9, 3754	4.9	18
247	Optically Active Defects at the SiC/SiO ₂ Interface. <i>Physical Review Applied</i> , 2019 , 12,	4.3	10
246	The Role of Near-Interface Traps in Modulating the Barrier Height of SiC Schottky Diodes. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1675-1680	2.9	10
245	Growth and characterization of nitrogen-phosphorus hybrid passivated gate oxide film on N-type 4H-SiC epilayer. <i>Journal of Crystal Growth</i> , 2019 , 507, 98-102	1.6	1
244	Direct Measurement of Active Near-Interface Traps in the Strong-Accumulation Region of 4H-SiC MOS Capacitors. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 468-474	2.3	14

243	Highly sensitive p-type 4H-SiC van der Pauw sensor.. <i>RSC Advances</i> , 2018 , 8, 3009-3013	3.7	15
242	Comparative study on slow-state near interface hole traps in NO and Ar annealed N-type 4H-SiC MOS capacitors by ultraviolet light. <i>Journal of Materials Science: Materials in Electronics</i> , 2018 , 29, 14292-14299 ⁴	2.1	4
241	Effect of Hole-Injection on Leakage Degradation in a $\text{p}^+\text{-GaN}$ Gate AlGaIn/GaN Power Transistor. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1203-1206	4.4	13
240	Mechanism of Threshold Voltage Shift in $\text{p}^+\text{-GaN}$ Gate AlGaIn/GaN Transistors. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1145-1148	4.4	61
239	A large pseudo-Hall effect in n-type 3C-SiC(1 0 0) and its dependence on crystallographic orientation for stress sensing applications. <i>Materials Letters</i> , 2018 , 213, 11-14	3.3	8
238	Mechanism of leakage current increase in p-GaN gate AlGaIn/GaN power devices induced by ON-state gate bias. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 124101	1.4	8
237	Stress and thermal characterization of 4H-SiC microelectromechanical structures. <i>Materials Letters</i> , 2017 , 191, 196-199	3.3	2
236	Experimental Investigation of Piezoresistive Effect in p-Type 4H-SiC. <i>IEEE Electron Device Letters</i> , 2017 , 38, 955-958	4.4	33
235	The Effect of Charge Redistribution on Flat-Band Voltage Turnaround in 4H-SiC MOS Capacitors. <i>Materials Science Forum</i> , 2017 , 897, 167-170	0.4	1
234	Piezo-Hall effect and fundamental piezo-Hall coefficients of single crystal n-type 3C-SiC(100) with low carrier concentration. <i>Applied Physics Letters</i> , 2017 , 110, 162903	3.4	3
233	Recognizing isolated words with minimum distance similarity metric padding. <i>Journal of Intelligent and Fuzzy Systems</i> , 2017 , 32, 2933-2939	1.6	1
232	Pseudo-Hall Effect in Single Crystal n-Type 3C-SiC(100) Thin Film. <i>Key Engineering Materials</i> , 2017 , 733, 3-7	0.4	3
231	Optimum top and bottom oxide thicknesses and flat-band voltages for improving subthreshold characteristics of 5 nm DG MOSFET. <i>Superlattices and Microstructures</i> , 2017 , 101, 285-292	2.8	
230	Comparative study of electrical characteristics for n-type 4H-SiC planar and trench MOS capacitors annealed in ambient NO. <i>Chinese Physics B</i> , 2017 , 26, 107101	1.2	3
229	Ultrathin Fe ₂ O ₃ nanoflakes using smart chemical stripping for high performance lithium storage. <i>Journal of Materials Chemistry A</i> , 2017 , 5, 18737-18743	13	48
228	Prediction of High-Density and High-Mobility Two-Dimensional Electron Gas at Al _x Ga _{1-x} N/4H-SiC Interface. <i>Materials Science Forum</i> , 2017 , 897, 719-722	0.4	3
227	Excellent Rectifying Properties of the n-3C-SiC/p-Si Heterojunction Subjected to High Temperature Annealing for Electronics, MEMS, and LED Applications. <i>Scientific Reports</i> , 2017 , 7, 17734	4.9	30
226	SiC power MOSFETs: The current status and the potential for future development 2017 ,		10

225	Piezoresistive effect in p-type 3C-SiC at high temperatures characterized using Joule heating. <i>Scientific Reports</i> , 2016 , 6, 28499	4.9	47
224	Growth mechanism for alternating supply epitaxy: the unique pathway to achieve uniform silicon carbide films on multiple large-diameter silicon substrates. <i>RSC Advances</i> , 2016 , 6, 16662-16667	3.7	5
223	Piezo-Hall effect in single crystal p-type 3C-SiC(100) thin film grown by low pressure chemical vapor deposition. <i>RSC Advances</i> , 2016 , 6, 31191-31195	3.7	9
222	Gate-Voltage Independence of Electron Mobility in Power AlGaN/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1013-1019	2.9	12
221	Active defects in MOS devices on 4H-SiC: A critical review. <i>Microelectronics Reliability</i> , 2016 , 60, 1-9	1.2	40
220	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. <i>Applied Surface Science</i> , 2016 , 365, 296-305	6.7	8
219	Temperature and doping dependence of the Raman scattering in 4H-SiC. <i>Optical Materials Express</i> , 2016 , 6, 2725	2.6	8
218	Comment on Catastrophic degradation of the interface of epitaxial silicon carbide on silicon at high temperatures[Appl. Phys. Lett. 109, 011604 (2016)]. <i>Applied Physics Letters</i> , 2016 , 109, 196101	3.4	2
217	Fundamental piezo-Hall coefficients of single crystal p-type 3C-SiC for arbitrary crystallographic orientation. <i>Applied Physics Letters</i> , 2016 , 109, 092903	3.4	3
216	The Power Law of Phonon-Limited Electron Mobility in the 2-D Electron Gas of AlGaN/GaN Heterostructure. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2214-2218	2.9	12
215	Influence of external mechanical stress on electrical properties of single-crystal n-3C-SiC/p-Si heterojunction diode. <i>Applied Physics Express</i> , 2015 , 8, 061302	2.4	9
214	Transient-Current Method for Measurement of Active Near-Interface Oxide Traps in 4H-SiC MOS Capacitors and MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2670-2674	2.9	45
213	A catalytic alloy approach for graphene on epitaxial SiC on silicon wafers. <i>Journal of Materials Research</i> , 2015 , 30, 609-616	2.5	43
212	Power-switching applications beyond silicon: Status and future prospects of SiC and GaN devices. <i>MRS Bulletin</i> , 2015 , 40, 399-405	3.2	46
211	A method for extraction of electron mobility in power HEMTs. <i>Superlattices and Microstructures</i> , 2015 , 85, 543-550	2.8	8
210	The Piezoresistive Effect of SiC for MEMS Sensors at High Temperatures: A Review. <i>Journal of Microelectromechanical Systems</i> , 2015 , 24, 1663-1677	2.5	150
209	The effect of device geometry and crystal orientation on the stress-dependent offset voltage of 3C-SiC(100) four terminal devices. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 8804-8809	7.1	23
208	Si Surface Preparation for Heteroepitaxial Growth of SiC Using In Situ Oxidation. <i>Materials Science Forum</i> , 2015 , 821-823, 205-208	0.4	1

207	The Dependence of Offset Voltage in p-Type 3C-SiC van der Pauw Device on Applied Strain. <i>IEEE Electron Device Letters</i> , 2015 , 36, 708-710	4.4	23
206	Memristor pattern recogniser: isolated speech word recognition. <i>Electronics Letters</i> , 2015 , 51, 1370-1372	1.1	11
205	Pseudo-Hall effect in single crystal 3C-SiC(111) four-terminal devices. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 12394-12398	7.1	16
204	Kinetic surface roughening and wafer bow control in heteroepitaxial growth of 3C-SiC on Si(111) substrates. <i>Scientific Reports</i> , 2015 , 5, 15423	4.9	8
203	Vertically Conductive Single-Crystal SiC-Based Bragg Reflector Grown on Si Wafer. <i>Scientific Reports</i> , 2015 , 5, 17026	4.9	12
202	Orientation dependence of the pseudo-Hall effect in p-type 3C-SiC four-terminal devices under mechanical stress. <i>RSC Advances</i> , 2015 , 5, 56377-56381	3.7	24
201	The effect of strain on the electrical conductance of p-type nanocrystalline silicon carbide thin films. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 1172-1176	7.1	27
200	Piezoresistive Effect of p-Type Single Crystalline 3C-SiC Thin Film. <i>IEEE Electron Device Letters</i> , 2014 , 35, 399-401	4.4	42
199	Thickness dependence of the piezoresistive effect in p-type single crystalline 3C-SiC nanoscale thin films. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 7176-7179	7.1	47
198	Power-switching applications beyond silicon: The status and future prospects of SiC and GaN devices 2014 ,		6
197	Misorientation dependent epilayer tilting and stress distribution in heteroepitaxially grown silicon carbide on silicon (111) substrate. <i>Thin Solid Films</i> , 2014 , 564, 39-44	2.2	18
196	Enhanced photoelectrocatalytic performance of etched 3C-SiC thin film for water splitting under visible light. <i>RSC Advances</i> , 2014 , 4, 54441-54446	3.7	10
195	Impact of Interface Traps on Current-Voltage Characteristics of 4H-SiC Schottky-Barrier Diodes. <i>Materials Science Forum</i> , 2014 , 778-780, 710-713	0.4	3
194	Fundamental piezoresistive coefficients of p-type single crystalline 3C-SiC. <i>Applied Physics Letters</i> , 2014 , 104, 111905	3.4	59
193	Selection of SPICE Parameters and Equations for Effective Simulation of Circuits with 4H-SiC Power MOSFETs. <i>Materials Science Forum</i> , 2014 , 778-780, 997-1000	0.4	
192	Growth of Gate Oxides on 4H-SiC by NO at Low Partial Pressures. <i>Materials Science Forum</i> , 2014 , 778-780, 627-630	0.4	5
191	RF sputtering of polycrystalline (100), (002), and (101) oriented AlN on an epitaxial 3C-SiC (100) on Si(100) substrate. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 06F401	1.3	5
190	Novel Electrical Characterization of Thin 3C-SiC Films on Si Substrates. <i>Science of Advanced Materials</i> , 2014 , 6, 1542-1547	2.3	11

189	Effect of Oxidation Time on Thermally Grown Oxide on GaN. <i>Journal of Materials Engineering and Performance</i> , 2013 , 22, 1341-1347	1.6	7
188	Energy position of the active near-interface traps in metal/oxide/semiconductor field-effect transistors on 4H-SiC. <i>Applied Physics Letters</i> , 2013 , 103, 113506	3.4	34
187	Color Chart for Thin SiC Films Grown on Si Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 279-282	0.4	6
186	The Impact of the Surface Treatments on the Properties of GaN/3C-SiC/Si Based Schottky Barrier Diodes. <i>Materials Science Forum</i> , 2013 , 740-742, 1111-1114	0.4	1
185	The fabrication and characterization of 4H-SiC power UMOSFETs. <i>Chinese Physics B</i> , 2013 , 22, 027302	1.2	8
184	Hydrogen Incorporation Dependence on the Thermal Growth Route in Dielectric/SiC Structures. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, N3041-N3044	2	
183	Biologically inspired features used for robust phoneme recognition. <i>International Journal of Machine Intelligence and Sensory Signal Processing</i> , 2013 , 1, 46		3
182	Implementing template matching logic in a standard flash memory cell. <i>Facta Universitatis - Series Electronics and Energetics</i> , 2013 , 26, 215-225	0.4	1
181	Influence of post-deposition annealing in oxygen ambient on metal/organic decomposed CeO ₂ film spin coated on 4H-SiC. <i>Journal of Materials Science: Materials in Electronics</i> , 2012 , 23, 257-266	2.1	20
180	SiC-based Piezoelectric Energy Harvester for Extreme Environment. <i>Procedia Engineering</i> , 2012 , 47, 1165-1172	10	
179	Formation of Zr-oxynitride thin films on 4H-SiC substrate. <i>Thin Solid Films</i> , 2012 , 520, 6822-6829	2.2	22
178	Ranked selection of nearest discriminating features. <i>Human-centric Computing and Information Sciences</i> , 2012 , 2, 12	5.4	9
177	Nearest Neighbor Classifier Based on Nearest Feature Decisions. <i>Computer Journal</i> , 2012 , 55, 1072-1087	1.3	20
176	Influence of various plasma treatment on the properties of carbon nanotubes for composite applications. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 1507-12	1.3	4
175	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 259-265	2.9	50
174	Demonstration of p-type 3C-SiC grown on 150 mm Si(1 0 0) substrates by atomic-layer epitaxy at 1000 °C. <i>Journal of Crystal Growth</i> , 2011 , 329, 67-70	1.6	53
173	Growth of 3C-SiC on 150-mm Si(100) substrates by alternating supply epitaxy at 1000 °C. <i>Thin Solid Films</i> , 2011 , 519, 6443-6446	2.2	78
172	InGaN/GaN Multiple Quantum Well Blue LEDs on 3C-SiC/Si Substrate. <i>Materials Science Forum</i> , 2011 , 679-680, 801-803	0.4	

171	Experimental Evaluation of Different Passivation Layers on the Performance of 3kV 4H-SiC BJTs. <i>Materials Science Forum</i> , 2010 , 645-648, 661-664	0.4	7
170	Improved 4H-SiC MOS Interface Produced by Oxidized-SiN Gate Oxide. <i>Materials Science Forum</i> , 2010 , 645-648, 511-514	0.4	2
169	Consequences of NO Thermal Treatments in the Properties of Dielectric Films / SiC Structures. <i>Materials Science Forum</i> , 2010 , 645-648, 689-692	0.4	4
168	Ag/PEPC/NiPc/ZnO/Ag thin film capacitive and resistive humidity sensors. <i>Journal of Semiconductors</i> , 2010 , 31, 054002	2.3	15
167	Effects of rapid thermal annealing on Al ₂ O ₃ /SiN reaction barrier layer/thermal-nitrided SiO ₂ stacking gate dielectrics on n-type 4H-SiC. <i>Applied Physics Letters</i> , 2010 , 96, 122108	3.4	6
166	NITRIDATION OF SILICON WITH AMMONIA AND NITROGEN. <i>International Journal of Nanoscience</i> , 2010 , 09, 169-174	0.6	
165	MOS Characteristics of Metallorganic-Decomposed CeO ₂ Spin-Coated on GaN. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H116		19
164	Effect of Postoxidation Annealing on High Temperature Grown SiO ₂ /4H-SiC Interfaces. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H196	3.9	11
163	Cognitive memory network. <i>Electronics Letters</i> , 2010 , 46, 677	1.1	10
162	Physical characterization of post-deposition annealed metal-organic decomposed cerium oxide film spin-coated on 4H-silicon carbide. <i>Journal of Alloys and Compounds</i> , 2010 , 497, 195-200	5.7	20
161	I-V characteristics of Ag/OD-MO/Ag surface-type diode fabricated by deposition of organic film from solution under the effect of an electric field. <i>EPJ Applied Physics</i> , 2010 , 50, 30401	1.1	0
160	Synthesis of Zn(II) 5,10,15,20-tetrakis(4-isopropylphenyl) porphyrin and its use as a thin film sensor. <i>Applied Physics A: Materials Science and Processing</i> , 2010 , 98, 103-109	2.6	35
159	Formation and characterization of SiO _x nanowires and Si/SiO _x core-shell nanowires via carbon-assisted growth. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1338-1342	3	15
158	Inter-image outliers and their application to image classification. <i>Pattern Recognition</i> , 2010 , 43, 4101-4112	12.7	27
157	Metal-oxide-semiconductor characteristics of thermally grown nitrided SiO ₂ thin film on 4H-SiC in various N ₂ O ambient. <i>Thin Solid Films</i> , 2010 , 518, 3255-3259	2.2	24
156	Role of Resolution in Noisy Pattern Matching. <i>Communications in Computer and Information Science</i> , 2010 , 120-124	0.3	
155	Effects of nitrogen incorporation on the interfacial layer between thermally grown dielectric films and SiC. <i>Applied Physics Letters</i> , 2009 , 94, 251909	3.4	30
154	Growth Mechanism of Cubic-Silicon Carbide Nanowires. <i>Journal of Nanomaterials</i> , 2009 , 2009, 1-5	3.2	10

153	Irreversible event-based model for thermal emission of electrons from isolated traps. <i>Journal of Applied Physics</i> , 2009 , 105, 103706	2.5	1
152	Effect of Post Deposition Annealing on the Characteristics of Sol-Gel Derived HfO ₂ on 4H-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 545-548	0.4	2
151	Characterization of anodic SiO ₂ films on P-type 4H-SiC. <i>Thin Solid Films</i> , 2009 , 517, 2808-2812	2.2	10
150	Transition between amorphous and crystalline phases of SiC deposited on Si substrate using H ₃ SiCH ₃ . <i>Journal of Crystal Growth</i> , 2009 , 311, 4442-4446	1.6	19
149	Microwave Properties of Bismuth Lanthanum Titanate Ceramic Substrate and its Effects with Various Shapes. <i>Journal of Electromagnetic Waves and Applications</i> , 2009 , 23, 415-425	1.3	
148	Stimulation of silicon carbide nanotubes formation using different ratios of carbon nanotubes to silicon dioxide nanopowders. <i>Journal of Alloys and Compounds</i> , 2009 , 475, 565-568	5.7	15
147	Effects of temperature and crucible height on the synthesis of 6H-SiC nanowires and nanoneedles. <i>Journal of Alloys and Compounds</i> , 2009 , 481, 345-348	5.7	8
146	Aluminum induced in situ crystallization of amorphous SiC. <i>Applied Physics Letters</i> , 2009 , 94, 181909	3.4	10
145	Charge Trapping Properties of 3C- and 4H-SiC MOS Capacitors With Nitrided Gate Oxides. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3185-3191	1.7	18
144	The microsatellite, macrophage migration inhibitory factor -794, may influence gene expression in human mononuclear cells stimulated with E. coli or S. pneumoniae. <i>International Journal of Immunogenetics</i> , 2008 , 35, 309-16	2.3	15
143	Genetic variation in heat shock protein 70 is associated with septic shock: narrowing the association to a specific haplotype. <i>International Journal of Immunogenetics</i> , 2008 , 35, 465-73	2.3	18
142	Synthesis and characterization of silica/titania nanocomposite via a combination of sol-gel and mechanochemical process. <i>Journal of Alloys and Compounds</i> , 2008 , 466, 304-307	5.7	7
141	Current mechanisms in n-SiC/p-Si heterojunctions. <i>Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on</i> , 2008 ,		8
140	Electrical Characteristics of Near-Interface Traps in 3C-SiC Metal Oxide Semiconductor Capacitors. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1021-1023	4.4	13
139	Characteristics of Sol-Gel Derived SiO ₂ Thick Film on 4H-SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 811-814	0.4	1
138	Effect of Post-Oxidation Annealing on High-Temperature Grown SiO ₂ /4H-SiC Interface. <i>Materials Science Forum</i> , 2008 , 600-603, 731-734	0.4	2
137	Investigation of Microwave Properties of High Permittivity Ceramic Substrate. <i>Journal of Electromagnetic Waves and Applications</i> , 2008 , 22, 1873-1882	1.3	1
136	Structural characterisation of anodic SiO ₂ thin films on n-type Si. <i>Surface Engineering</i> , 2008 , 24, 388-391	2.6	

135	MOS Capacitor Characteristics of 3C-SiC Films Deposited on Si Substrates at 1270°C. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1069, 1		
134	Turn-Around of Threshold Voltage in Gate Bias Stressed p-Channel Power Vertical Double-Diffused MetalOxideSemiconductor Transistors. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 6272-6276	1.4	8
133	Face Recognition Using Local Binary Decisions. <i>IEEE Signal Processing Letters</i> , 2008 , 15, 821-824	3.2	14
132	Investigation of sol-gel derived HfO ₂ on 4H-SiC. <i>Applied Surface Science</i> , 2008 , 254, 1981-1985	6.7	19
131	Effects of heat treatment in vacuum on the physical properties of thermal nitrided silicon dioxide gate on 4H-silicon carbide. <i>Thin Solid Films</i> , 2008 , 516, 7921-7924	2.2	1
130	Analysis of charge conduction mechanisms in nitrided SiO ₂ Film on 4H SiC. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2008 , 372, 529-532	2.3	20
129	Effects of annealing temperature on ultra-low dielectric constant SiO ₂ thin films derived from sol-gel spin-on-coating. <i>Physica B: Condensed Matter</i> , 2008 , 403, 611-615	2.8	14
128	The accuracy of surrogate decisions in intensive care scenarios. <i>Anaesthesia and Intensive Care</i> , 2007 , 35, 46-51	1.1	12
127	Deep void formation mechanism in Si(100) during its carbonization reaction with C ₂ H ₂ . <i>Thin Solid Films</i> , 2007 , 515, 6824-6826	2.2	2
126	Effects of precursor aging and post-deposition treatment time on photo-assisted sol-gel derived low-dielectric constant SiO ₂ thin film on Si. <i>Microelectronics Journal</i> , 2007 , 38, 227-230	1.8	7
125	A diplotype in the lymphotoxin alpha gene is associated with differential expression of LTA mRNA induced by Gram-positive and Gram-negative bacteria. <i>International Journal of Immunogenetics</i> , 2007 , 34, 157-60	2.3	3
124	Analysis of current conduction mechanisms in atomic-layer-deposited Al ₂ O ₃ gate on 4H silicon carbide. <i>Applied Physics Letters</i> , 2007 , 90, 162113	3.4	33
123	Sequential thermal treatments of SiC in NO and O ₂ : Atomic transport and electrical characteristics. <i>Applied Physics Letters</i> , 2007 , 91, 041906	3.4	16
122	Effects of Thermally Oxidized-SiN Gate Oxide on 4H-SiC Substrate. <i>Electrochemical and Solid-State Letters</i> , 2007 , 10, H327		4
121	Electrical Properties of Atomic-Layer-Deposited La ₂ O ₃ /Thermal-Nitrided SiO ₂ Stacking Dielectric on 4H-SiC(0001). <i>Materials Science Forum</i> , 2007 , 556-557, 643-646	0.4	8
120	Effects of thermal nitrided gate-oxide thickness on 4H silicon-carbide-based metal-oxide-semiconductor characteristics. <i>Applied Physics Letters</i> , 2007 , 90, 012120	3.4	28
119	Effects of rapid thermal annealing on nitrided gate oxide grown on 4H-SiC. <i>Microelectronic Engineering</i> , 2006 , 83, 65-71	2.5	15
118	Silicon carbide as a material for mainstream electronics. <i>Microelectronic Engineering</i> , 2006 , 83, 123-125	2.5	10

117	Electrical stressing effects in commercial power VDMOSFETs. <i>IET Circuits, Devices and Systems</i> , 2006 , 153, 281		17
116	Analysis of subthreshold carrier transport for ultimate DGMOSFET. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 685-691	2.9	31
115	Investigation of SiO ₂ -SiC Interface by High-Resolution Transmission Electron Microscope. <i>Materials Science Forum</i> , 2006 , 527-529, 975-978	0.4	
114	Effects of electrical stressing in power VDMOSFETs. <i>Microelectronics Reliability</i> , 2005 , 45, 115-122	1.2	20
113	Characteristics of Post-Nitridation Rapid-Thermal Annealed Gate Oxide Grown on 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 689-692	0.4	4
112	SiC/SiO ₂ Interface States: Properties and Models. <i>Materials Science Forum</i> , 2005 , 483-485, 563-568	0.4	29
111	Current conduction mechanisms in post-nitridation rapid-thermal-annealed gate oxides on 4H silicon carbide. <i>Applied Physics Letters</i> , 2005 , 87, 212102	3.4	15
110	Electronic Properties of SiON/HfO ₂ Insulating Stacks on 4H-SiC (0001). <i>Materials Science Forum</i> , 2004 , 457-460, 1361-1364	0.4	8
109	A P-Channel MOSFET on 4H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 1401-1404	0.4	17
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5	Effects of electrical stressing in power VDMOSFETs		2
4	Spontaneous recovery of positive gate bias stressed power VDMOSFETs		2
3	Channel-carrier mobility parameters for 4H SiC MOSFETs		4
2	KOH wet etching techniques for the micromachining of (100) SOI wafers		3
1	Applications of high frequency magnetic components for switching resonant mode power supply		3